

PSMNR82-30YLE

N-channel 30 V, 0.82 mOhm, ASFET with enhanced SOA in LFPAK56

25 July 2022

Preliminary data sheet

1. General description

N-channel enhancement mode ASFET with enhanced SOA in LFPAK56 package optimized for low R_{DSon} and strong safe operating area optimized for hot-swap, inrush and linear-mode applications.

2. Features and benefits

- Fully optimized Safe Operating Area (SOA) for superior linear mode operation
- Optimized for low R_{DSon} / low I²R conduction losses
- LFPAK56E package for applications that demand the highest performance and reliability in a 30 mm² footprint
- Low leakage < 1 µA at 25 °C
- Copper-clip for low parasitic inductance and resistance
- High reliability LFPAK package, qualified to 175 °C

3. Applications

- Hot swap in 12 V-20 V applications
- e-Fuse
- DC switch
- · Load switch
- · Battery protection

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	330	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	268	W
Tj	junction temperature			-55	-	175	°C
Static char	acteristics		•				
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10		-	0.75	0.82	mΩ
		$V_{GS} = 7 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 10$		-	0.87	1.25	mΩ
Dynamic cl	haracteristics			'	'		
Q _{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V;		2	10	20	nC
Q _{G(tot)}	total gate charge	Fig. 12; Fig. 13		18	41	68	nC



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain diode							
S	softness factor	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; Fig. 16$		-	1.03	-	

^{[1] 330} A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	
2	S	source	ال الله الله الله الله الله الله الله ا	D
3	S	source	a	
4	G	gate		G_(□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□
mb	D	mounting base; connected to drain	LFPAK56; Power- SO8 (SOT669)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PSMNR82-30YLE	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMNR82-30YLE	E82L30Y

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 $^{\circ}$ C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	30	V
V_{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	268	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	330	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	295	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	1667	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode			'		
I _S	source current	T _{mb} = 25 °C		-	268	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	1667	Α
Avalanche r	uggedness			•		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 25 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 5.5 ms	[2]	-	2.7	J
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 30 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega$	[2]	-	190	Α

^{[1] 330} A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

^[2] Protected by 100% test

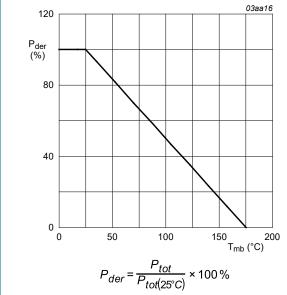
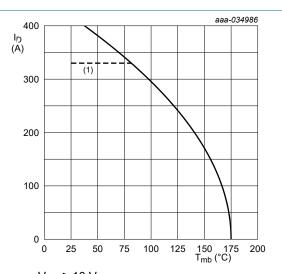
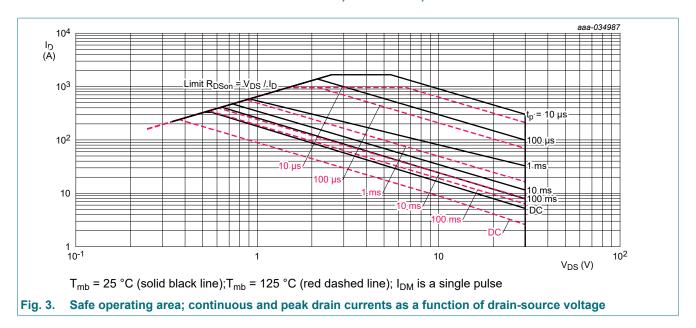


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$ (1) 330 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

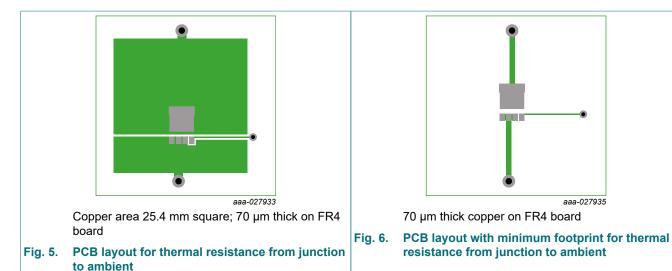


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.42	0.56	K/W
R _{th(j-a)}	thermal resistance from	Fig. 5	-	42	-	K/W
	junction to ambient	Fig. 6	-	85	-	K/W





10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charact	eristics		•	_	'	'
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 2 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.2	1.79	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-3.7	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 24 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 24 V; V _{GS} = 0 V; T _j = 125 °C	-	7.2	-	μΑ
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10	-	0.75	0.82	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; Fig. 11	-	-	1.48	mΩ
		V _{GS} = 7 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 10</u>	-	0.87	1.25	mΩ
		V_{GS} = 7 V; I_D = 25 A; T_j = 150 °C; Fig. 11	-	-	2.25	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	1.3	3.2	8	Ω
Dynamic char	acteristics			_		'
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	18	41	68	nC
		I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 12; Fig. 13	41	90	149	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	46	-	nC

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V;		5	19	36	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13		2.7	10	19	nC
Q _{GS(th-pl)}	post-threshold gate- source charge	-		2.4	9	17	nC
Q_{GD}	gate-drain charge			2	10	20	nC
V _{GS(pI)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>		-	3.2	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;		4052	6754	10131	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>		1234	2056	3084	pF
C _{rss}	reverse transfer capacitance			93	343	823	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 0.6 Ω ; V_{GS} = 4.5 V;		-	49	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	95	-	ns
t _{d(off)}	turn-off delay time			-	37	-	ns
t _f	fall time			-	44	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	49	-	nC
Source-dra	in diode			'			
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.78	1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	35	-	ns
Q _r	recovered charge	V _{DS} = 15 V; <u>Fig. 16</u>	[1]	-	28	-	nC
t _a	reverse recovery rise time			-	17.3	-	ns
t _b	reverse recovery fall time			-	17.9	-	ns
S	softness factor	1		-	1.03	-	

[1] includes capacitive recovery

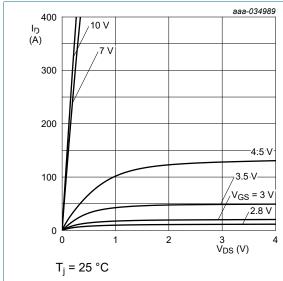


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

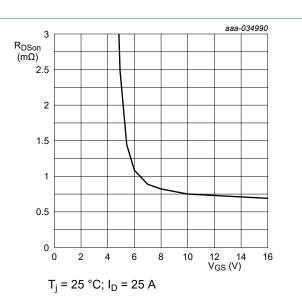


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

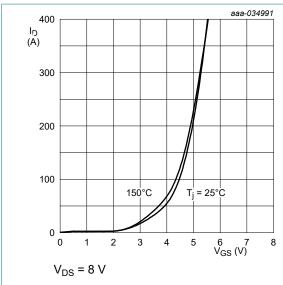


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

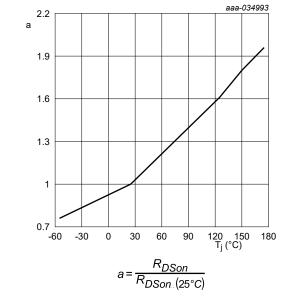


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

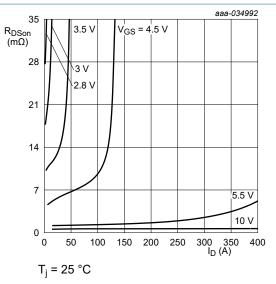


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

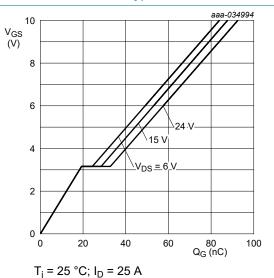


Fig. 12. Gate-source voltage as a function of gate charge; typical values

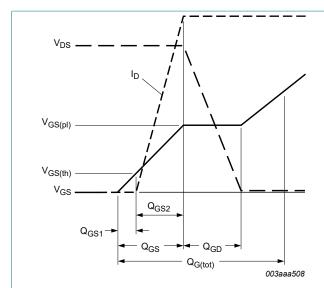
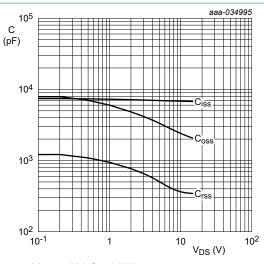


Fig. 13. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

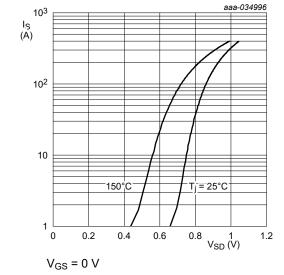


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

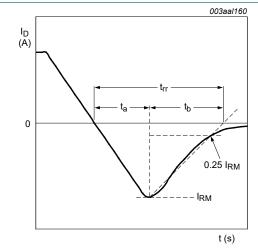


Fig. 16. Reverse recovery timing definition

11. Package outline

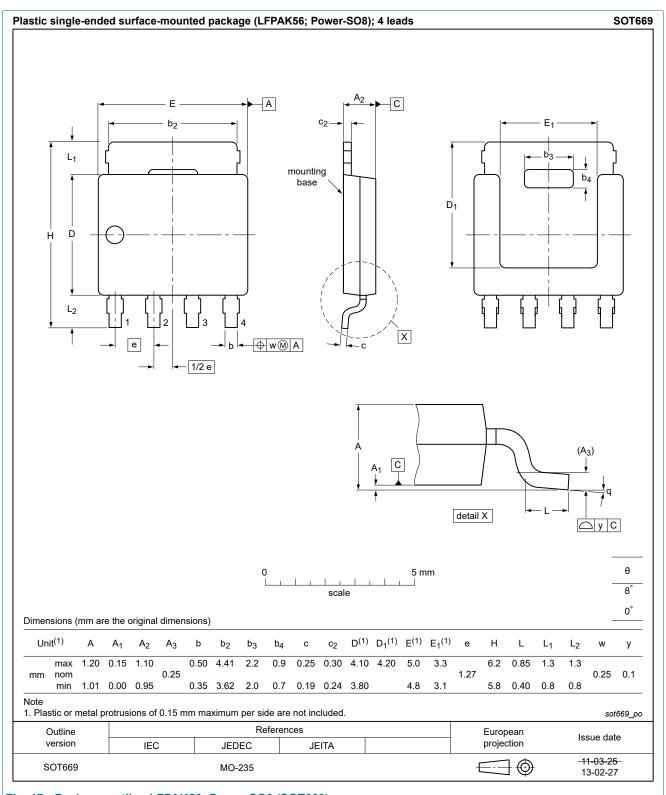
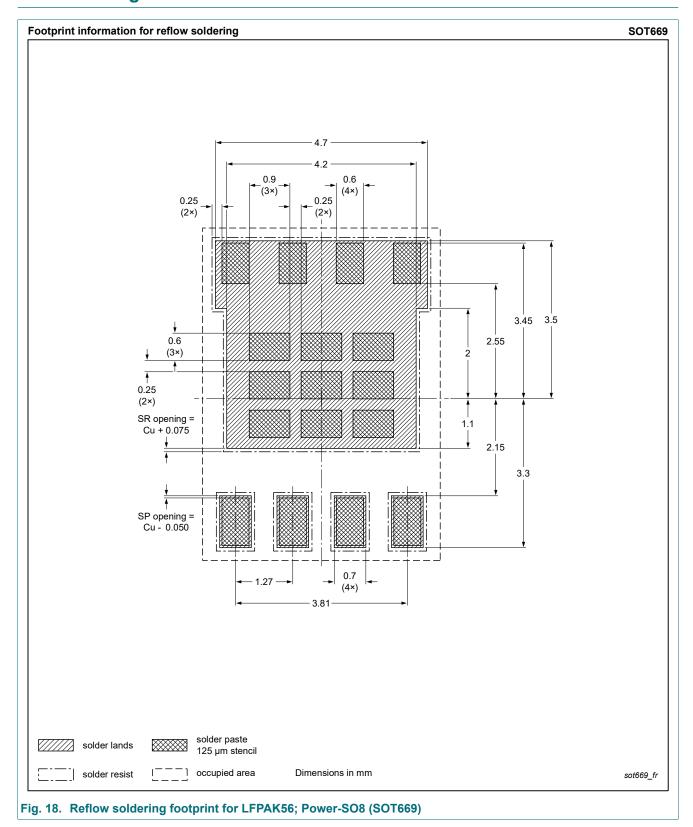
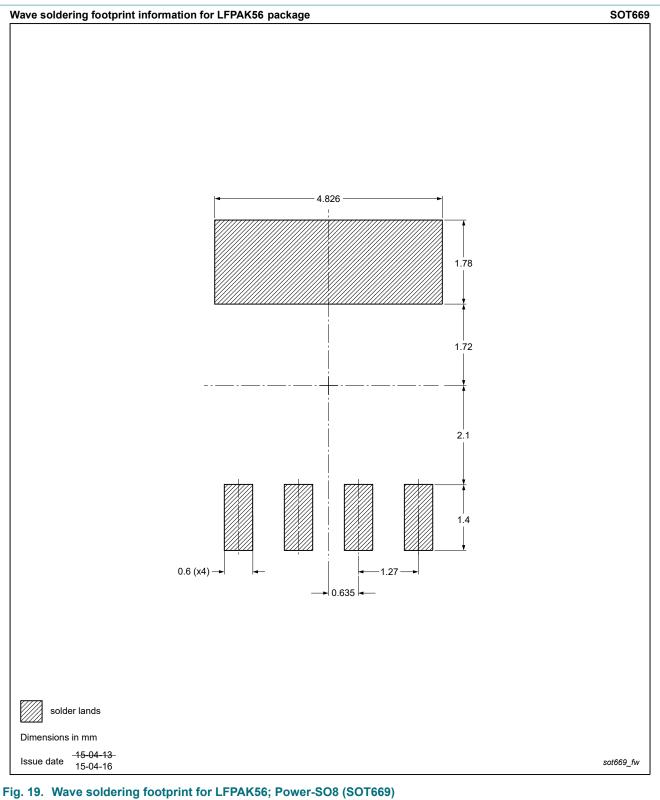


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

12. Soldering





13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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